



SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary we will further optimize the design of our InP laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.



## **TO-9 Packaged Laser Diode**

High Power Single-Mode and Multi-Mode SemiNex

12xx to 19xx nm

Custom Wavelengths Available Lensed Options Available

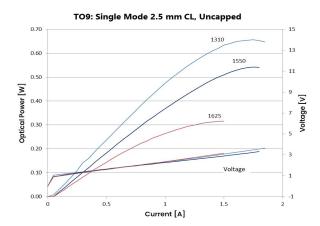
## **Applications**

- OEM Medical Professional Medical LiDAR

- Military / Aerospace Illumination

## Features

- Cost effective
- High Output Power
- High Dynamic Range
- High Efficiency Standard Low Cost Package



## Non-Pulsed TO9





	Symbol	TO9-105	Units
0-4:1	Symbol	109-105	Units
Optical			
Wavelength	$\lambda_{C}$	1565	nm (±20)
Output Power (CW)	P∘	0.40	watts (±10%)
Chip Cavity Length	CL	2500	μm
Emitter Width	W	4	μm
Emitter Height	Н	1	μm
Spectral Width	δλ	10	nm 3dB
Slope Efficiency	η.	0.30	W/A
Fast Axis Div.*	Θ_perp	30	deg FWHM
Slow Axis Div.	Θ_parallel	10	deg FWHM
Electrical			
Power Conversion Eff.	η	13	%
Operating Current	I <sub>op</sub>	1.2	A
Threshold Current	l <sub>th</sub>	0.05	A
Operating Voltage	$V_{op}$	2.5	V
Mechanical			
Weight		1.5	g
Operating Temp.**		-40 to 60	°C
Storage Temp.		-40 to 80	°C

Specified values are rated at a constant heat sink temperature of 20°C.

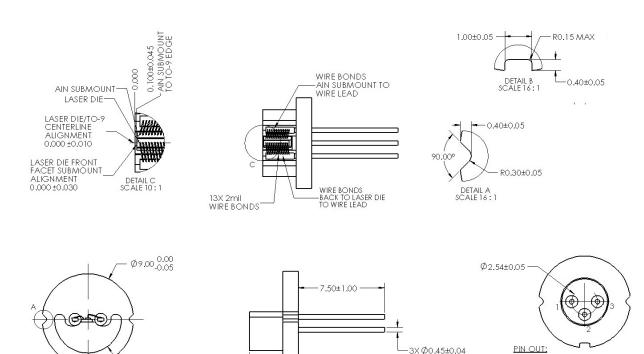
\*\*Specified operating conditions are based on 20°C heat sink temperature. High temperature operation will reduce performance and MTTF.

Unless otherwise indicated all values are nominal.

Uncapped TO9 specifications assume heatsinking undermeath laser chip.

Capped TO9 specifications assume heatsinking only on flat surface where pins extend.

3X Ø0.45±0.04



- 1.50±0.05

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3.30±0.05

R3.29±0.05